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TW	A73	5,951,757		09/14/	1999	Dubl	belday et al.					
TN	A74	6,461,945		10/08/2	2002	Yu					-	
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FORM PTO - 1449

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-012DV

APPLICANT(S): Lee et al.

SERIAL NO.: 10/788,741

FILING DATE: February 27, 2004

GROUP: 2813

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
NI	A75	2002/0063292	05/30/2002	Armstrong et al.			
1	A76	2002/0190284	12/19/2002	Murthy et al.			
	A77	2004/0007724	01/15/2004	Murthy et al.			
$\neg \uparrow$	A78	2004/0014276	01/22/2004	Murthy et al.			
	A79	2004/0070035	04/15/2004	Murthy et al.			-
	A80	2004/0084735	05/06/2004	Murthy et al.	-		
	A81	2004/0119101	06/24/2004	Schrom et al.			
	A82	2004/0142545	07/22/2004	Ngo et al.			
	A83 2004/0173815 09/09/2		09/09/2004	Yeo et al.			
_	A84	5,089,872	02/18/1992	Ozturk et al.			
	A85	5,242,847	09/07/1993	Ozturk et al.			
	A86	6,228,694	05/08/2001	Doyle et al.			<u></u>
	A87	6,235,568	05/22/2001	Murthy et al.			
-	A88	6,281,532	08/28/2001	Doyle et al.			
	A89	6,326,664	12/04/2001	Chau et al.			
+-	A90	6,563,152	05/13/2003	Roberds et al.			
+-	A91	6,605,498	08/12/2003	Murthy et al.			
 . 	A92	6,621,131	09/16/2003	Murthy et al.			
		12/02/2003	Wang et al.	- 			
+	A94	6,703,648	03/09/2004	Xiang et al.			
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	C75	Gannavaram, et al. Source/Drain Tech Digest, (2000), pp.	nology for su								
JN/	C76	Ge et al., "Process- International Elect							ngineering	," <u>IEE</u> E	
TN	C77	Ghani et al., "A 90 Strained Silicon Cl 978-980.									
7N	C78	Hamada et al., "A Electron Devices,"	•					d MOS De	vices," <u>IEE</u>	E Tran	sactions on
TN	C79	Huang et al., "Isola Device Letters, Vo		-			Aobility in	Thin-Film	SOI Devic	es," <u>IE</u> I	EE Electron
77	C80	Huang et al., "LOCOS-Induced Stress Effects on Thin-Film SOI Devices," <u>IEEE Transactions on Electron</u> <u>Devices</u> , Vol. 44, No. 4 (April 1997), pp. 646-650.									
\mathcal{M}	C81	Huang, et al., "Reduction of Source/Drain Series Resistance and Its Impact on Device Performance for PMOS Transistors with Raised Si _{1-x} Ge _x Source/Drain", <u>IEEE Electron Device Letters</u> , Vol. 21, No. 9, (Sept. 2000) pp. 448-450.									
71	C82	lida et al., "Therms mobility," Solid-St						or bonded v	vafer and e	ffects o	n electron
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7	C83	Ito et al., "Mechani Design," <u>IEEE Inte</u>			-			-		sistor			
M	C84	Lochtefeld et al., "I NMOS via Mechan			-		-						
-TN	C85	Ootsuka et al., "A Fon-a-Chip Applicat 578.											
TN	C86	Ota et al., "Novel L International Electr	•		•	_		5nm CMO	S," <u>IEE</u>	E			
TN	C87	Öztürk, et al., "Adv International Electr					-	Sub-70 nm	CMOS	," <u>IEEE</u>			
TN	C88	Öztürk, et al., "Low Resistivity Nickel Germanosilicide Contacts to Ultra-Shallow Si _{1-x} Ge _x Source/Drain Junctions for Nanoscale CMOS," <u>IEEE International Electron Device Meeting Technical Digest</u> (2003), pp. 497-500.											
N	C89	Öztürk, et al., "Selective Silicon-Gremanium Source/Drain Technology for Nanoscale CMOS," Mat. Res. Soc. Symp. Proc., Vol. 717, (2002), pp. C4.1.1-C4.1.12.											
W	C90	Öztürk, et al., "Ultr Germanium Techno pp. 77-82.						-					
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-M	C91	Shimizu et al., "Lo Enhancement," <u>IEI</u>					-					
W	C92	Thompson <i>et al.</i> , ". 25, No. 4 (April 20	-		Featuring Str	ained-Silic	on," <u>IEEE</u>	Electron D	evice L	etters, Vol.		
74	C93	Thompson et al., ", of Cu Interconnect Technical Digest, (s, Low k ILD,	and lum ² S								
TN	C94	Tiwari et al., "Hole Strain," <u>IEEE Inter</u>								sing Local		
TN	C95	Uchino, et al., "A I CMOS ULSIs," <u>IE</u>										
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FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-012DV

APPLICANTS: Lee et al.

SERIAL NO.: Not yet assigned 10/ 788741

2-27-04
FILING DATE: Herewith GROUP: Not yet assigned

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71	Al	4,710,788		12/01/1	987	Dāmbl	es et al.	·				
TN	A2	4,990,979	•	02/05/1	991	Otto					Ĺ	
77	A3	5,241,197		08/31/1	1993	Murak	ami et al.				<u> </u>	
TN	A4	5,291,439		03/01/1	994	Kauffn	nann et al.			··		
TN	A5	5,442,205		08/15/1	995	Brasen	et al.				ļ	٠.
TN	A6	5,523,592		06/04/1	1996	Nakag	awa et al.					· .
TN	A7	5,534,713		07/09/1	1996	Ismail	et al.				<u>]</u>	
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77	B1	41 01 167 A1	07/2	3/1992	DE					No		Yes (abstract only
72	B2	4-307974	10/3	30/1992 ЈР						No		No
72/	В3	7-106446	04/2	21/1995 JP						No		No
72/	B4	0 683 522 A2	11/2	2/1995	EP			· <u>·</u>		No		Yes
7	B5	0 829 908 A2	03/1	8/1998	EP			<u> </u>		No		Yes
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EXAM. INIT.	ОТ	HER DOCUMENT	S: (In	cluding	Auth	or, Title,	Date, Rele	evant Page	s, Place o	f Publica	tion)	
TN	CI	Meyerson et al., Physics Letters.	Vol. 5	3, No. 25	(Dec	ember 19), 1988) pp.	2555-255	7.			<u> </u>
TN	C2	Garone et al., "S Letters, Vol. 56,	No. 13	March	26, 1	990) pp.	1275-1277	•	. ,			
TN	C3	Robbins et al., "A Vol. 69, No. 6 (N	March	15, 19 91) pp. 3	3729-373	2.					· · · · · · · · · · · · · · · · · · ·
TN.	C4	"2 Bit/Cell EEPI Bulletin, Vol. 35	, No. 4	IB (Septe	ember	1992) p	p. 136-140.					
7N	C5	Wesler et al., "N Structures," <u>Elec</u>	tròn D	evices N	1cetin	<u>r. 1992.</u>	Technical I	Digest (Dec	ember 13,	1992) pp	. 31.7.1	-31.7.3.
71/	C6	Grützmacher et a growth atmosphe	il., "Go re," <u>A</u>	segrega pplied P	tion in	n SiGe/S Letters	Vol. 63, No	ctures and o. 18 (Nov	its depend ember 1, 1	ence on d 993) pp.	epositio 2531-25	on technique and 533.
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TN	A8	5,596,527		01/12/1	997	Tomiol	ca et al.				· ·	· · · ·
$\overline{\mathcal{M}}$.A9	5,617,351		04/01/1	997	Bertin	et al.					
JN/	A10	5,683,934		11/04/1	997	Candel	aria					
77	All	5,739,567		04/14/1	998	Wong						<u> </u>
77/	A12	5,777,347		07/07/1	998	Barteli	Bartelink					· ·
DIV	A13	5,786,612		07/28/1	998	Otani e	Otani et al.				ļ <u>.</u>	··
TW.	A14	5,792,679	08/11/	998	Nakato) 				<u> </u>		
\sqrt{N}	A15	5,808,344	09/15/	998	Ismail	ct al.						
TW	A16	5,891,769				Liaw c	Liaw et al.					
TN	A17	5,906,951	5,906,951 05/25/1999				ai			<u> </u>		
TW	A18	5,998,807		12/07/	999	Lustig	et al:				<u> </u>	
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-TN	B6	0 838 858 A2	04/2	9/1998	EP					No		Yes
77	B7	11-233744	08/2	7/1999	ЛР					No	<u>.</u>	No
M	B8	WO 98/59365	12/3	0/1998	PCT			<u> </u>		No		Yes
70	В9	WO 99/53539	10/2	1/1999	PCI	•				No		Yes
71	B10	2001319935	05/2	2000	JР	·				Yes		No
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71	/ C7	MOSFETs," Ele	ctron	<u>Devices r</u>	<u>neetin</u>	Space Hot-Electron Transfer in High Mobility, Strained-Si Multilayer etings, 1993, Technical Digest (December 1993) pp. 21.3.1-21.3.4.					1.3.4.	
72	C	Journal of Vacu	um Sc	ience and	Tech	strained SiGe epitaxial layers on Si and misfit dislocation interactions," echnology A. Vol. 12, No. 4 (July/August 1994) pp. 1924-1931.						
7	/ C	Tweet et al., "Fa Applied Physics	ng the 5, No.	g the composition of strained GeSi layers grown with disilane and germane," No. 20 (November 14, 1994) pp. 2579-2581.					mo Remane'.			
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TN	A19	6,013,134		01/11/	2000	Chu et	al.	: ''':		<u> </u>		•
TN	A20	6,058,044		05/02/	2000	Sugiur	a et al.	: .				
\mathcal{M}	A21	6,059,895		05/09/7	2000	Chu et al.						
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Mo Yes												
B12 WO 00/54338 09/14/2000 PCT No Yes												
	B13	WO 01/54202 A1	07/2	6/2001	PCT			<u>-</u>		No		Yes
TN	B14	WO 01/93338 A1	12/0	6/2001	PCT			: :		No		Yes
TN	B15	WO 01/99169 A2	12/2	7/2001	PCT	. :				No		Yes
M	B16	1 174 928 A1	01/2	3/2002	EP			· ·		No		Yes
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77	Cl	IEDM Technical	Diges	(1995)	pp. 761	1-764.		·				
TN	CI											
70	CI	Laboratory, Stant	ford U	niversity	, Stanf	ord, CA	94305 (199	95) pp. 20	.3.1-20.3.4	· '		·
7~	CI	Semiconductor F	ield-E	ffect Trai	nsistor	s," Ph.D	. Thesis, St	anford Ur	niversity (19	995) pp. 1-	205.	٠.
N	CI	IEEE Transaction	s on E	lectron l	Device	s, Vol. 4	3, No. 8 (A	ugust 199	96) pp. 122	4-1232.		
71/	CI:	10 (October 1996	5) pp. 1	709-171	6.		•					
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TN	CI	Semicon. Sci. Te	chnol.	(1997) (abstrac		quantum w	ells with r	neighboring	confinem	eni siri	caure,
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FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-012DV

APPLICANTS: Lee et al.

SERIAL NO.: Not yet assigned 10/788741
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TIV	A2	2 6,096,590		08/01/	2000	Chan e	at al.			· ,		
TN	A2	3 6,107,653		08/22/	2000	Fitzge	rald			,		
77/	A2	4 6,111,267	•	08/29/	2000	Fische	r et al.		,			·
77	A2:	5 6,117,750		09/12/	2000	Bensal	hel et al.	· .				·. ·
TN	A20	6 6,130,453	:	10/10/	2000	Mei et	al.					
TN	A2	7 6,143,636		11/07/	2000	Forbes	et al.			 .		
W.	. A2	8 6,204,529		03/20/	2001	Lung	t al.			<u> </u>	1.	
TW.	A2	9 6,207,977 B1		03/27/	2001	Augus						· · · · · · · · · · · · · · · · · · ·
77	A3	0 US 2001/0003364	Al	06/14/			ara et al.					· · · · · · · · · · · · · · · · · · ·
7~	/ A3	1 6,249,022		06/19/	2001	Lin et						
TN	A3:			06/26/			wa et al.			·-		
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7 N	A3		2 A1	08/01/			ald et al.			·		·
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TN	B17	WO 02/15244A2	02/2	1/2002	PCT	•				No		Yes
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W	B19	WO 02/47168 A2	06/1	3/2002	PCT				1	No		Yes
, N	B20	WO 02/071488 A1	09/12	2/2002	PCT					No		Yes
TN	B21	WO 02/071491 A1	09/12	2/2002	PCT					No		Yes
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INFORMATION DISCLOSURE STATEMENT APPLICANTS: Lee et al. SERIAL NO.: Not yet assigned 10/789 741 FILING DATE: Herewith GROUP: Not yet assigned U.S. PATENT DOCUMENTS CLASS SUB FILING DATE IF DOCUMENT DATE NAME EXAM. CLASS APPROPRIATE NUMBER INIT. 02/26/2002 Chu et al. A36 6,350,993 B1 12/04/2001 A37 US 2002/0125471 A1 09/12/2002 Fitzgerald et al. 03/31/2001 US 2002/140031 A1 10/03/2002 Rim A38 07/16/2001 A39 US 2002/0125497 A1 09/12/2002 Fitzgerald FOREIGN PATENT DOCUMENTS FILING ABSTRACT **ENGLISH SUB** COUNTRY CLASS EXAM. DOCUMENT DATE LANG (Y/N) DATE ONLY CODE CLASS INIT. NUMBER No Yes **PCT** 09/12/2002 **B22** WO 02/071495 A1 OTHER ART, JOURNAL ARTICLES, ETC. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) EXAM. INIT. Maiti et al., "Strained-Si heterostructure field effect transistors," Semicond. Sci. Technol., Vol. 13 (1998) pp. C20 1225-1246. Hackbarth et al., "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," Journal of C21 Crystal Growth, Vol. 201 (1999) pp. 734-738 Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," Submitted to the Massachusetts Institute of Technology Department of Electrical Engineering and Computer Science on June 30, 1999, pp. 1-154. O'Neill et al., "SiGe Virtual substrate N-channel heterojunction MOSFETS," Semicond. Sci. Technol., Vol. 14 C23 (1999) pp. 784-789. Rim, "Application of Silicon Based Heterostrucutres to Enhanced Mobility Metal-Oxide-Semiconductor Field-C24 Effect Transistors," Ph.D. Thesis, Stanford University (July 1999) pp. 1-184 Parker et al., "SiGe heterostructure CMOS circuits and applications," Solid State Electronics, Vol. 43, No. 8, C25 (August 1999) pp. 1497-1506. 6/22/06 DATE CONSIDERED **EXAMINER**

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FORM PTO - 1449 ATTORNEY DOCKET NO.: ASC-012DV INFORMATION DISCLOSURE STATEMENT APPLICANTS: Lee et al. SERIAL NO.: Not yet assigned 2-27-04

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71	C70	Pelekanos et al. Crystal Growth				Te/CdZnTe	strained qu	antum we	lis," <u>J</u> c	ournal of
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INFORM	ATIO	N DISCLOSUR	APPLICANTS: Lee et al. 10/788741								
\			SERIAL NO.: Not yet assigned								
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			GROUP: Not yet assigned								
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-N	B26	9-219524	08/19/1997	JP ·				No		Yes, Abstract Only	
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